

Line Number	Hits	Search Text	DB	Time stamp
1	14755	"micro-electromechanical system" or MEMS	USPAT; EPO; JPO; IBM_TDB	2002/12/29 12:29
2	1009	(polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG) and (HF or hydrofluoric) and etch\$3 and releas\$5	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:20
3	120	((polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG) and (HF or hydrofluoric) and etch\$3 and releas\$5; and microstructure	USPAT; EPO; JPO; IBM_TDB	2002/12/29 12:32
-	1	6146917.pn.	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:17
8	69	(polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG) and (HF or hydrofluoric) and etch\$3 and releas\$5 and strict\$3	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:19
9	122	("micro-electromechanical system" or MEMS) and ((polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG) and (HF or hydrofluoric) and etch\$3 and releas\$5)	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:19
10	829	((438/51) or (438/52) or (438/53) or (438/456)).CCLS.	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:20
11	33	((polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG) and (HF or hydrofluoric) and etch\$3 and releas\$5) and (((438/51) or (438/52) or (438/53) or (438/456)).CCLS.)	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:20
12	1131	(polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG or sacrificial or sacrificed) and (HF or hydrofluoric) and etch\$3 and releas\$5	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:21
13	182	("micro-electromechanical system" or MEMS) and ((polysilicon or photoresist) and ("silicon oxide" or "SiO.sub.2" or TEOS or phosphosilicate or PSG or sacrificial or sacrificed) and (HF or hydrofluoric) and etch\$3 and releas\$5)	USPAT; EPO; JPO; IBM_TDB	2002/12/29 13:21